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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

147 papers	2,534 citations	27 h-index	46 g-index
165 ext. papers	2,865 ext. citations	5.1 avg, IF	4.68 L-index

#	Paper	IF	Citations
147	Diffusion, coalescence, and reconstruction of vacancy defects in graphene layers. <i>Physical Review Letters</i> , 2005 , 95, 205501	7.4	416
146	Detailed Atomic Reconstruction of Extended Line Defects in Monolayer MoS ₂ . <i>ACS Nano</i> , 2016 , 10, 5419-5430	11.7	115
145	Effects of As/P exchange reaction on the formation of InAs/InP quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 2029-2031	3.4	104
144	Dynamics and stability of divacancy defects in graphene. <i>Physical Review B</i> , 2011 , 84,	3.3	80
143	Atomic Structure and Spectroscopy of Single Metal (Cr, V) Substitutional Dopants in Monolayer MoS. <i>ACS Nano</i> , 2016 , 10, 10227-10236	16.7	77
142	Vacancy defects and the formation of local haeckelite structures in graphene from tight-binding molecular dynamics. <i>Physical Review B</i> , 2006 , 74,	3.3	77
141	Optical gain in InGaNGaN quantum well structures with embedded AlGaInN layer. <i>Applied Physics Letters</i> , 2007 , 90, 023508	3.4	74
140	Ultra-high-throughput Production of III-V/Si Wafer for Electronic and Photonic Applications. <i>Scientific Reports</i> , 2016 , 6, 20610	4.9	66
139	Improved performance of AlGaIn-based deep ultraviolet light-emitting diodes with nano-patterned AlN/sapphire substrates. <i>Applied Physics Letters</i> , 2017 , 110, 191103	3.4	63
138	Hydrogen-free graphene edges. <i>Nature Communications</i> , 2014 , 5, 3040	17.4	63
137	Stability and dynamics of the tetravacancy in graphene. <i>Nano Letters</i> , 2014 , 14, 1634-42	11.5	57
136	Atomic Structure of Graphene Subnanometer Pores. <i>ACS Nano</i> , 2015 , 9, 11599-607	16.7	56
135	Reconstruction and evaporation at graphene nanoribbon edges. <i>Physical Review B</i> , 2010 , 81,	3.3	53
134	Investigation of leakage current paths in n-GaN by conductive atomic force microscopy. <i>Applied Physics Letters</i> , 2014 , 104, 102101	3.4	49
133	Simulation and fabrication of highly efficient InGaIn-based LEDs with corrugated interface substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2874-2877		40
132	Measuring the junction temperature of III-nitride light emitting diodes using electro-luminescence shift. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 1869-1873	1.6	39
131	The role of the bridging atom in stabilizing odd numbered graphene vacancies. <i>Nano Letters</i> , 2014 , 14, 3972-80	11.5	36

130	Partial Dislocations in Graphene and Their Atomic Level Migration Dynamics. <i>Nano Letters</i> , 2015 , 15, 5950-5	11.5	33
129	Less strained and more efficient GaN light-emitting diodes with embedded silica hollow nanospheres. <i>Scientific Reports</i> , 2013 , 3, 3201	4.9	33
128	The formation of pentagon-heptagon pair defect by the reconstruction of vacancy defects in carbon nanotube. <i>Applied Physics Letters</i> , 2008 , 92, 043104	3.4	33
127	Microstructured Air Cavities as High-Index Contrast Substrates with Strong Diffraction for Light-Emitting Diodes. <i>Nano Letters</i> , 2016 , 16, 3301-8	11.5	33
126	Changes in the growth mode of low temperature GaN buffer layers with nitrogen plasma nitridation of sapphire substrates. <i>Applied Physics Letters</i> , 1997 , 71, 1228-1230	3.4	32
125	Formation of carbon nanotube semiconductor-metal intramolecular junctions by self-assembly of vacancy defects. <i>Physical Review B</i> , 2007 , 76,	3.3	30
124	Low temperature photoluminescence characteristics of Zn-doped InP grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 1998 , 83, 2261-2265	2.5	30
123	Formation and development of dislocation in graphene. <i>Applied Physics Letters</i> , 2013 , 102, 021603	3.4	28
122	Optical and microstructural studies of atomically flat ultrathin In-rich InGa _{0.1} N/GaN multiple quantum wells. <i>Journal of Applied Physics</i> , 2008 , 103, 063509	2.5	28
121	Thermally Induced Dynamics of Dislocations in Graphene at Atomic Resolution. <i>ACS Nano</i> , 2015 , 9, 10066-10075	11.5	27
120	Room temperature near-ultraviolet emission from In-rich InGa _{0.1} N/GaN multiple quantum wells. <i>Applied Physics Letters</i> , 2005 , 86, 192105	3.4	25
119	Changes in Preferred Orientation of Pt Thin Films Deposited by dc Magnetron Sputtering Using Ar/O ₂ Gas Mixtures. <i>Journal of Materials Research</i> , 1999 , 14, 1255-1260	2.5	25
118	Growth of In-rich InGa _{0.1} N/GaN quantum dots by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2004 , 269, 95-99	1.6	24
117	The effects of low temperature buffer layer on the growth of pure Ge on Si(001). <i>Thin Solid Films</i> , 2010 , 518, 6496-6499	2.2	23
116	Electrically driven mid-submicrometre pixelation of InGa _{0.1} N micro-light-emitting diode displays for augmented-reality glasses. <i>Nature Photonics</i> ,	33.9	22
115	Highly (200)-oriented Pt films on SiO ₂ /Si substrates by seed selection through amorphization and controlled grain growth. <i>Journal of Materials Research</i> , 1999 , 14, 634-637	2.5	21
114	Atomic Level Distributed Strain within Graphene Divacancies from Bond Rotations. <i>ACS Nano</i> , 2015 , 9, 8599-608	16.7	20
113	Incorporation of air-cavity into sapphire substrate and its effect on GaN growth and optical properties. <i>Journal of Crystal Growth</i> , 2015 , 430, 41-45	1.6	20

112	Compositional analysis of In-rich InGaN layers grown on GaN templates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2008 , 310, 3004-3008	1.6	18
111	In-rich InGaN/GaN quantum wells grown by metal-organic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2006 , 99, 044906	2.5	17
110	Elongated Silicon-Carbon Bonds at Graphene Edges. <i>ACS Nano</i> , 2016 , 10, 142-9	16.7	15
109	Single-Crystalline Nanobelts Composed of Transition Metal Ditellurides. <i>Advanced Materials</i> , 2018 , 30, e1707260	24	15
108	Complete suppression of large InAs island formation on GaAs by metal organic chemical vapor deposition with periodic AsH ₃ interruption. <i>Applied Physics Letters</i> , 2007 , 90, 033105	3.4	15
107	Monolithic integration of visible GaAs and near-infrared InGaAs for multicolor photodetectors by using high-throughput epitaxial lift-off toward high-resolution imaging systems. <i>Scientific Reports</i> , 2019 , 9, 18661	4.9	15
106	The role of pentagon-heptagon pair defect in carbon nanotube: The center of vacancy reconstruction. <i>Applied Physics Letters</i> , 2010 , 97, 093106	3.4	14
105	Control of Crack Formation for the Fabrication of Crack-Free and Self-Isolated High-Efficiency Gallium Arsenide Photovoltaic Cells on Silicon Substrate. <i>IEEE Journal of Photovoltaics</i> , 2016 , 6, 1031-1035	3.7	14
104	Rotating Anisotropic Crystalline Silicon Nanoclusters in Graphene. <i>ACS Nano</i> , 2015 , 9, 9497-506	16.7	13
103	Effects of growth interruption on the evolution of InAs/InP self-assembled quantum dots. <i>Journal of Electronic Materials</i> , 2000 , 29, 535-541	1.9	13
102	Atomic Structure and Dynamics of Epitaxial Platinum Bilayers on Graphene. <i>ACS Nano</i> , 2019 , 13, 12162-12170	26.7	12
101	High quality Ge epitaxial layers on Si by ultrahigh vacuum chemical vapor deposition. <i>Thin Solid Films</i> , 2009 , 517, 3990-3994	2.2	12
100	Selective growth of N-polar InN through an in situ AlN mask on a sapphire substrate. <i>Applied Physics Letters</i> , 2014 , 104, 032108	3.4	11
99	Characteristics of blue and ultraviolet light-emitting diodes with current density and temperature. <i>Electronic Materials Letters</i> , 2010 , 6, 51-53	2.9	11
98	Gaseous Nanocarving-Mediated Carbon Framework with Spontaneous Metal Assembly for Structure-Tunable Metal/Carbon Nanofibers. <i>Advanced Materials</i> , 2017 , 29, 1702958	24	10
97	Room temperature operation of mid-infrared InAsSb based photovoltaic detectors with an InAlSb barrier layer grown on GaAs substrates. <i>Optics Express</i> , 2018 , 26, 6249-6259	3.3	9
96	Epitaxial growth of single-crystalline AlN layer on Si(111) by DC magnetron sputtering at room temperature. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 060306	1.4	9
95	Dissociation reaction of B ₂ H ₆ on TiN surfaces during atomic layer deposition: first-principles study. <i>RSC Advances</i> , 2017 , 7, 55750-55755	3.7	9

94	Effects of growth temperature on surface morphology of InP grown on patterned Si(0 0 1) substrates. <i>Journal of Crystal Growth</i> , 2015 , 416, 113-117	1.6	9
93	Growth of Si-doped GaInP on Ge-on-Si substrates and its photoluminescence characteristics. <i>Applied Physics Letters</i> , 2011 , 99, 091904	3.4	9
92	Anomalous strain profiles and electronic structures of a GaAs-capped InAs/In _{0.53} Ga _{0.47} As quantum ring. <i>Journal of Applied Physics</i> , 2011 , 109, 103701	2.5	9
91	Si adatom diffusion on Si (100) surface in selective epitaxial growth of Si. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003 , 21, 2388		9
90	Arsenic incorporation and growth mode of GaNAs grown by low-pressure metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2003 , 248, 437-440	1.6	9
89	Effect of growth interruption on In-rich InGaN/GaN single quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2830-2833		9
88	Shape change of InAs self-assembled quantum dots induced by As/P exchange reaction. <i>Thin Solid Films</i> , 1999 , 357, 81-84	2.2	9
87	Effects of nitrogen doping in amorphous carbon layers on the diffusion of fluorine atoms: A first-principles study. <i>Journal of Applied Physics</i> , 2019 , 125, 155701	2.5	8
86	In Situ Atomic Level Dynamics of Heterogeneous Nucleation and Growth of Graphene from Inorganic Nanoparticle Seeds. <i>ACS Nano</i> , 2016 , 10, 9397-9410	16.7	8
85	Solid-phase epitaxy of a cavity-shaped amorphous alumina nanomembrane structure on a sapphire substrate. <i>Journal of Crystal Growth</i> , 2018 , 498, 130-136	1.6	8
84	Point defects in turbostratic stacked bilayer graphene. <i>Nanoscale</i> , 2017 , 9, 13725-13730	7.7	8
83	Anomalous strain relaxation and light-hole character enhancement in GaAs capped InAs/In _{0.53} Ga _{0.47} As quantum ring. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 76-78	2.5	8
82	Analysis of surface adsorption kinetics of SiH ₄ and Si ₂ H ₆ for deposition of a hydrogenated silicon thin film using intermediate pressure SiH ₄ plasmas. <i>Applied Surface Science</i> , 2019 , 496, 143728	6.7	7
81	An ultra-thin compliant sapphire membrane for the growth of less strained, less defective GaN. <i>Journal of Crystal Growth</i> , 2016 , 441, 52-57	1.6	7
80	MOCVD growth of GaN layer on InN interlayer and relaxation of residual strain. <i>Thin Solid Films</i> , 2010 , 518, 6365-6368	2.2	7
79	Isotropic/anisotropic growth behavior and faceting morphology of Si epitaxial layer selectively grown by cold wall ultrahigh vacuum chemical vapor deposition. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 275		7
78	Real time in situ monitoring of stacked InAs/InP quantum dots by spectral reflectance. <i>Journal of Crystal Growth</i> , 2003 , 248, 201-205	1.6	7
77	Growth of GaN epitaxial layers on sapphire with preheated ammonia and their structural and optoelectronic properties. <i>Current Applied Physics</i> , 2003 , 3, 351-354	2.6	7

76	The growth of In-rich InGaN/GaN single quantum wells by metalorganic chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2834-2837		7
75	Effects of thin GaAs insertion layer on InAs(InGaAs)InP(001) quantum dots grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2005 , 86, 223110	3.4	7
74	Analysis of P adsorption and desorption on the (001) InP surface using surface photoabsorption. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 2663-2667	2.9	7
73	Characterization of Platinum films Deposited by a Two-Step Magnetron Sputtering on SiO ₂ /Si Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 441, 341		7
72	Highly polarized photoluminescence from c-plane InGaN/GaN multiple quantum wells on stripe-shaped cavity-engineered sapphire substrate. <i>Scientific Reports</i> , 2019 , 9, 8282	4.9	6
71	Flaw-Containing Alumina Hollow Nanostructures Have Ultrahigh Fracture Strength To Be Incorporated into High-Efficiency GaN Light-Emitting Diodes. <i>Nano Letters</i> , 2018 , 18, 1323-1330	11.5	6
70	Infrared photoreflectance investigation of resonant levels and band edge structure in InSb. <i>Optics Letters</i> , 2015 , 40, 5295-8	3	6
69	Low-Temperature Metalorganic Chemical Vapor Deposition of Gallium Nitride on (0001) Sapphire Substrates Using a Remote RF Nitrogen Plasma. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 95		6
68	A discrete core-shell-like micro-light-emitting diode array grown on sapphire nano-membranes. <i>Scientific Reports</i> , 2020 , 10, 7506	4.9	5
67	Direct observation and catalytic role of mediator atom in 2D materials. <i>Science Advances</i> , 2020 , 6, eaba4942	4.4	5
66	Study of UV excited white light-emitting diodes for optimization of luminous efficiency and color rendering index. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 34-36	2.5	5
65	Violet-light spontaneous and stimulated emission from ultrathin In-rich InGaN/GaN multiple quantum wells grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2008 , 93, 161905	3.4	5
64	Epitaxial lateral overgrowth of GaN on nano-cavity patterned sapphire substrates. <i>Journal of Crystal Growth</i> , 2019 , 507, 103-108	1.6	5
63	The influence of hydrogen concentration in amorphous carbon films on mechanical properties and fluorine penetration: a density functional theory and molecular dynamics study.. <i>RSC Advances</i> , 2020 , 10, 6822-6830	3.7	4
62	Microstructured void gratings for outcoupling deep-trap guided modes. <i>Optics Express</i> , 2018 , 26, A450-A461	3.9	4
61	Linearly polarized photoluminescence of anisotropically strained c-plane GaN layers on stripe-shaped cavity-engineered sapphire substrate. <i>Applied Physics Letters</i> , 2018 , 112, 212102	3.4	4
60	Growth of GaN layer with preserved nano-columnar low temperature GaN buffer to reduce the wafer bowing. <i>Thin Solid Films</i> , 2013 , 546, 118-123	2.2	4
59	Characterization of deep levels in GaInP on Ge and Ge-on-Si substrates by photoluminescence and cathodoluminescence. <i>Journal of Crystal Growth</i> , 2013 , 370, 168-172	1.6	4

58	Catalyst-free growth of InN nanorods by metal-organic chemical vapor deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 50-55	1.6	4
57	Strong carrier localization and diminished quantum-confined Stark effect in ultra-thin high-indium-content InGaN quantum wells with violet light emission. <i>Applied Physics Letters</i> , 2013 , 103, 222104	3.4	4
56	Microstructural Investigation of Bilayer Growth of In- and Ga-Rich InGaN Grown by Chemical Vapor Deposition. <i>Journal of Electronic Materials</i> , 2009 , 38, 518-522	1.9	4
55	Thermodynamic study of AlGaIn composition grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2007 , 298, 367-371	1.6	4
54	Effect of Hydrogen on GaN Growth by Remote Plasma-Enhanced Metal-Organic Chemical Vapor Deposition. <i>Physica Status Solidi A</i> , 1999 , 176, 337-342		4
53	Noncontact minority carrier lifetime measurement of Si and SiGe epilayers prepared by ultrahigh vacuum electron cyclotron resonance chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996 , 14, 1033-1036	2.9	4
52	Surface structurization and control of CuS particle size by discharge mode of inductively coupled plasma and vapor-phase sulfurization. <i>Plasma Sources Science and Technology</i> , 2018 , 27, 114002	3.5	4
51	Heterogeneously integrated high-performance GaAs single-junction solar cells on copper. <i>Journal of the Korean Physical Society</i> , 2017 , 70, 693-698	0.6	3
50	Suppression of surface leakage current in InSb photodiode by ZnS passivation. <i>International Journal of Nanotechnology</i> , 2016 , 13, 392	1.5	3
49	Effects of H and N treatment for BH dosing process on TiN surfaces during atomic layer deposition: an study.. <i>RSC Advances</i> , 2018 , 8, 21164-21173	3.7	3
48	Effects of TMSb overpressure on InSb surface morphology for InSb epitaxial growth using low pressure metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2014 , 401, 518-522	1.6	3
47	Enhancement of optical properties of InAs quantum dots grown by using periodic arsine interruption. <i>Thin Solid Films</i> , 2009 , 517, 3963-3966	2.2	3
46	Growth mechanism of highly uniform InAs/GaAs quantum dot with periodic arsine interruption by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2011 , 110, 044302	2.5	3
45	(100) Oriented Platinum thin Films Deposited by Dc Magnetron Sputtering On SiO ₂ /Si Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 441, 335		3
44	Strain relaxation and dislocation annihilation in compositionally graded H _{0.5} (Al _x Ga _{1-x}) ₂ O ₃ layer for high voltage H _{0.5} Ga ₂ O ₃ power devices. <i>Acta Materialia</i> , 2021 , 221, 117423	8.4	3
43	First principles investigation on energetics, structure, and mechanical properties of amorphous carbon films doped with B, N, and Cl. <i>Scientific Reports</i> , 2019 , 9, 18961	4.9	3
42	Overall reaction mechanism for a full atomic layer deposition cycle of W films on TiN surfaces: first-principles study.. <i>RSC Advances</i> , 2018 , 8, 39039-39046	3.7	3
41	Solid-Phase Epitaxial Growth of an Alumina Layer Having a Stacking-Mismatched Domain Structure of the Intermediate β Phase. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 41487-41496	9.5	3

40	Selective Area Growth of Single-Crystalline Alpha-Gallium Oxide on a Sapphire Nanomembrane by Mist Chemical Vapor Deposition. <i>ACS Applied Electronic Materials</i> ,	4	3
39	Atomic Scale Imaging of Reversible Ring Cyclization in Graphene Nanoconstrictions. <i>ACS Nano</i> , 2019 , 13, 2379-2388	16.7	2
38	Monolithic Integration of GaAs//InGaAs photodetectors for multicolor detection 2019 ,		2
37	Enhanced Thermal Conductivity of the Underfill Materials Using Insulated Core/shell Filler Particles for High Performance Flip Chip Applications 2017 ,		2
36	Fabrication of a-plane InN nanostructures on patterned a-plane GaN template by ECR-MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 447-450	1.6	2
35	Investigation of InN mole fraction fluctuation in InGaN films grown by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1499-1502		2
34	Aspect ratio dependent strains in InAs/InP quantum dots measured by synchrotron radiation x-ray diffraction. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003 , 21, 183		2
33	Microscopic study on the behavior of the {311} facet in the selective epitaxial growth of Si(100). <i>Applied Physics Letters</i> , 2004 , 85, 4624-4626	3.4	2
32	The formation of cubic GaNAs phase during the growth of thin GaNAs epilayers on GaN at low temperatures by metalorganic chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 2462-2465		2
31	The emission wavelength tuning of InAs/InP quantum dots with thin GaAs, InGaAs, InP capping layers by MOCVD. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 169-173	3	2
30	Quantitative analysis of the compositional profile of a single quantum well by grazing incidence x-ray reflectivity and photoluminescence. <i>Applied Physics Letters</i> , 1999 , 74, 2152-2154	3.4	2
29	Nitrogen Plasma Pretreatment of Sapphire Substrates for the GaN Buffer Growth by Remote Plasma Enhanced MOCVD. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 53		2
28	Effects of r-plane Sapphire Substrate Tilt Angles on the Growth Behavior of Nonpolar a-plane GaN. <i>Journal of the Korean Physical Society</i> , 2011 , 58, 906-910	0.6	2
27	Crystalline silicon nanoparticle formation by tailored plasma irradiation: self-structurization, nucleation and growth acceleration, and size control. <i>Nanoscale</i> , 2021 , 13, 10356-10364	7.7	2
26	A new growth method of semi-insulating GaN layer for HEMT structure by eliminating degenerate layer at GaN/sapphire interface. <i>Current Applied Physics</i> , 2015 , 15, S11-S15	2.6	1
25	Reduction in threading dislocation density in ge epitaxial layers grown on Si(001) substrates by using rapid thermal annealing. <i>Journal of the Korean Physical Society</i> , 2015 , 67, 1646-1650	0.6	1
24	Growth of High Quality Ge Layer on Silica Nano-Spheres Integrated Ge/Si Template Using UHV-CVD. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P83-P85	2	1
23	Advanced Si solid phase crystallization for vertical channel in vertical NANDs. <i>APL Materials</i> , 2014 , 2, 076106	5.7	1

22	Ultraviolet stimulated emission in periodically polarity-inverted ZnO structures at room temperature. <i>Applied Physics Letters</i> , 2010 , 97, 171101	3.4	1
21	Competitive growth mechanisms of InAs quantum dots on InxGa1-xAs layer during post growth interruption. <i>Thin Solid Films</i> , 2010 , 518, 6361-6364	2.2	1
20	Improved Emission Efficiency in InGaN Light-Emitting Diodes Using Reverse Bias in Pulsed Voltage Operation. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1190-1192	2.2	1
19	In situ monitoring of the growth procedure of InAs layer by spectral reflectance. <i>Journal of Crystal Growth</i> , 2007 , 298, 50-53	1.6	1
18	Growth behavior and optical properties of In-rich InGaN quantum dots by metal-organic chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 112-115		1
17	Comparison of the Strain-modified Band Gap Energies of Truncated and Untruncated InAs Quantum Dots in GaAs Matrix at Varying Inter-dot Spacings. <i>Journal of the Physical Society of Japan</i> , 2004 , 73, 3378-3383	1.5	1
16	Stress of Platinum Thin Films Deposited by Dc Magnetron Sputtering Using Argon/Oxygen Gas Mixture. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 441, 427		1
15	Growth of Less Bowed GaN Epitaxial Layers on Sapphire Substrates by Formation of Low-Temperature GaN Buffer Layer with Columnar Microstructure. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 01AF01	1.4	1
14	Temperature-Dependent Polarized Photoluminescence from c-plane InGaN/GaN Multiple Quantum Wells Grown on Stripe-Shaped Cavity-Engineered Sapphire Substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900526	1.3	1
13	Effects of the flux-controlled cation off-stoichiometry in SrRuO3 grown by molecular beam epitaxy on its physical and electrical properties. <i>Materials Letters</i> , 2020 , 281, 128375	3.3	1
12	Fabrication of Less Bowed Light-Emitting Diodes on Sapphire Substrates with a SiO2 Thin Film on Their Back Sides. <i>Journal of the Korean Physical Society</i> , 2019 , 75, 480-484	0.6	1
11	Diffusion of adatom in the selective epitaxial growth of Si(100): A molecular dynamics study. <i>Applied Physics Letters</i> , 2006 , 88, 231909	3.4	0
10	Thermodynamic insights into interfacial interactions in TiN/amorphous Al2O3 heterostructures: ab initio molecular dynamics and first principles investigation. <i>Inorganic Chemistry Frontiers</i> , 2020 , 7, 4347-4356	6.8	0
9	Strain relaxation effects on TE-polarized light emission and in-plane polarization ratio in c-plane ultraviolet AlGaIn/AlN quantum well structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020 , 120, 114112	3	
8	Improved crystal quality of a-plane GaN with high- temperature 3-dimensional GaN buffer layers deposited by using metal-organic chemical vapor deposition. <i>Journal of the Korean Physical Society</i> , 2012 , 60, 1297-1300	0.6	
7	Analysis of failure of C-V characteristics of MIS structure with SiO2 passivation layer deposited on InSb substrate via Raman spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2014 , 1670, 25		
6	Effect of dimethylhydrazine on p-type conductivity of as-grown Mg-doped GaN. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 52-54	2.5	
5	Growth of Less Bowed GaN Epitaxial Layers on Sapphire Substrates by Formation of Low-Temperature GaN Buffer Layer with Columnar Microstructure. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 01AF01	1.4	

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- 3 Comparison of 500nm InGaN/GaN QW Emission Properties Induced by Piezoelectric Field Effect and Phase Separation. *Materials Research Society Symposia Proceedings*, **2000**, 639, 11191
- 2 Growth of Nitride Quantum Dots **2005**, 95-131
- 1 Strained Quantum Rings. *Nanoscience and Technology*, **2014**, 331-352 o.6